优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

0755-83047638
ysbdt@szyoushang.cn
www.szyoushang.cn

企业微信二维码

企业QQ二维码

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max T_C = +25°C
60V	19mΩ @ V_{GS} = 10V	33.2A
	28mΩ @ V_{GS} = 4.5V	28A

Features and Benefits

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production – Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low Input Capacitance
- Fast Switching Speed

Description and Applications

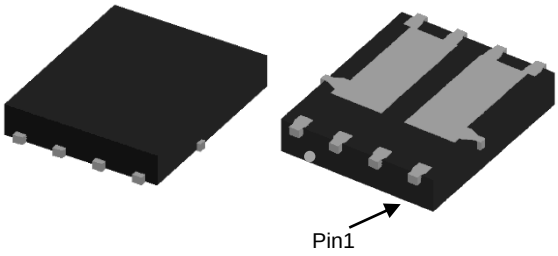
This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Engine management systems
- Body control electronics
- DC-DC converters

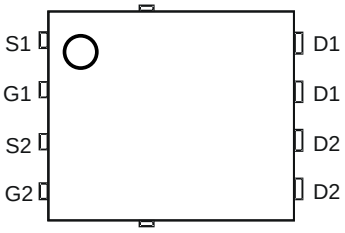
Mechanical Data

- Package: PowerDI®5060-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.097 grams (Approximate)

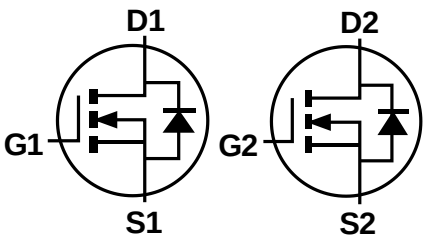
PowerDI5060-8 (Type C)



Top View Bottom View



Pinout
Top View



Equivalent Circuit

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	60	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (Note 6)	T_C = +25°C T_C = +100°C	I_D	33.2 23.7	A
Continuous Drain Current (Note 5)	T_A = +25°C T_A = +100°C	I_D	9.2 6.5	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I_{DM}	50	A
Maximum Continuous Body Diode Forward Current (Note 5)		I_S	31	A
Pulsed Body Diode Forward Current (Note 5)		I_{SM}	50	A
Avalanche Current, L = 0.1mH		I_{AS}	15.3	A
Avalanche Energy, L = 0.1mH		E_{AS}	11.7	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	2.5	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\Theta JA}$	58	°C/W
Total Power Dissipation (Note 6)	T_C = +25°C	P_D	37.5	W
Thermal Resistance, Junction to Case (Note 6)		$R_{\Theta JC}$	4	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +175	°C

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
6. Thermal resistance from junction to soldering point (on the exposed drain pad).

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	V_{GS} = 0V, I_D = 250μA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	V_{DS} = 48V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	1	—	2.5	V	V_{DS} = V_{GS}, I_D = 250μA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	14.5	19	mΩ	V_{GS} = 10V, I_D = 10A
		—	20.9	28		V_{GS} = 4.5V, I_D = 6A
Diode Forward Voltage	V_{SD}	—	0.7	1.2	V	V_{GS} = 0V, I_S = 20A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{ISS}	—	864	—	pF	V_{DS} = 30V, V_{GS} = 0V, f = 1MHz
Output Capacitance	C_{OSS}	—	282	—	pF	
Reverse Transfer Capacitance	C_{RSS}	—	27	—	pF	
Gate Resistance	R_G	—	1.3	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_G	—	8.4	—	nC	V_{DS} = 30V, I_D = 10A
Total Gate Charge (V_{GS} = 10V)	Q_G	—	17	—	nC	
Gate-Source Charge	Q_{GS}	—	3.1	—	nC	
Gate-Drain Charge	Q_{GD}	—	4.3	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	3.4	—	ns	V_{DD} = 30V, V_{GS} = 10V, I_D = 10A, R_G = 6Ω
Turn-On Rise Time	t_R	—	5.2	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	13	—	ns	
Turn-Off Fall Time	t_F	—	7	—	ns	
Body Diode Reverse Recovery Time	t_{RR}	—	22	—	ns	I_F = 10A, di/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q_{RR}	—	11	—	nC	

Notes: 7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

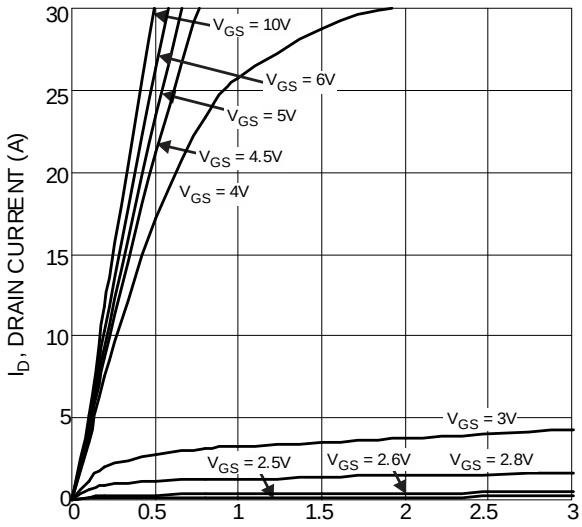


Figure 1 Typical Output Characteristic

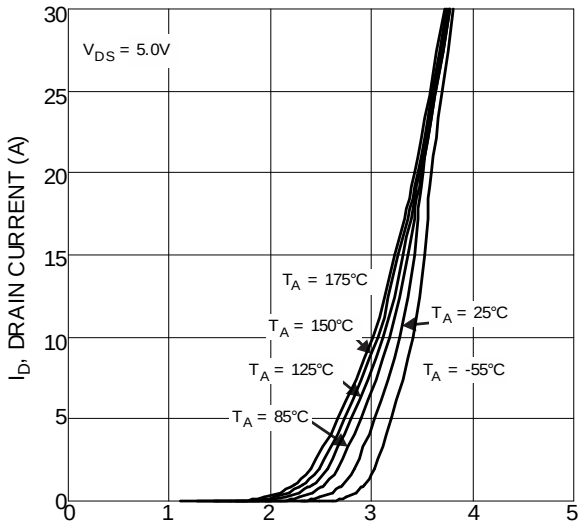


Figure 2 Typical Transfer Characteristics

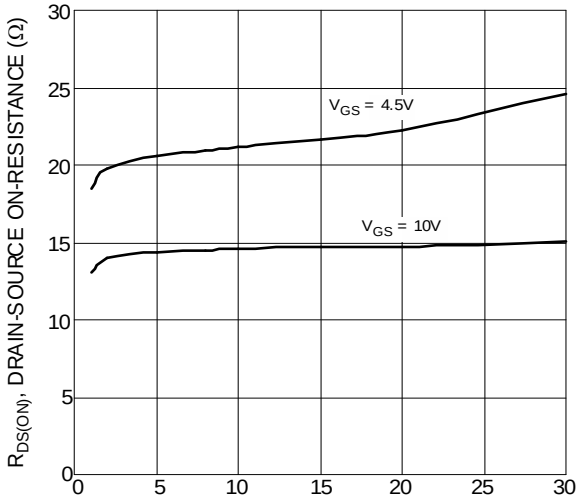


Figure 3 Typical On-Resistance vs.
Drain Current and Gate Voltage

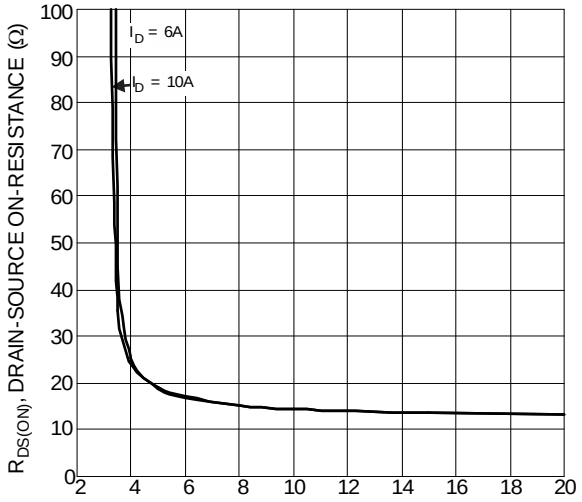


Figure 4 Typical Drain-Source On-Resistance
vs. Gate-Source Voltage

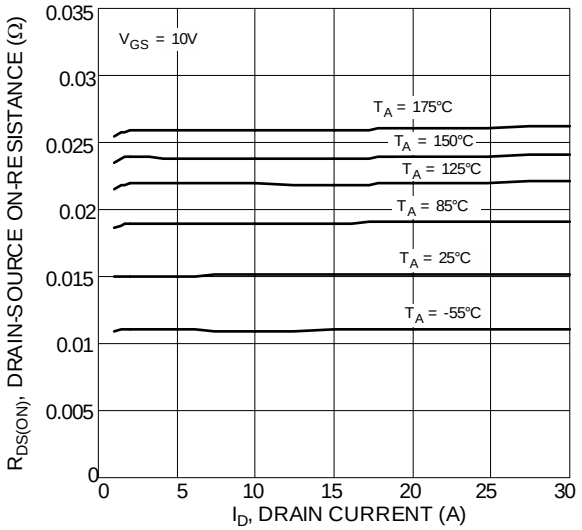


Figure 5 Typical On-Resistance vs.
Drain Current and Temperature

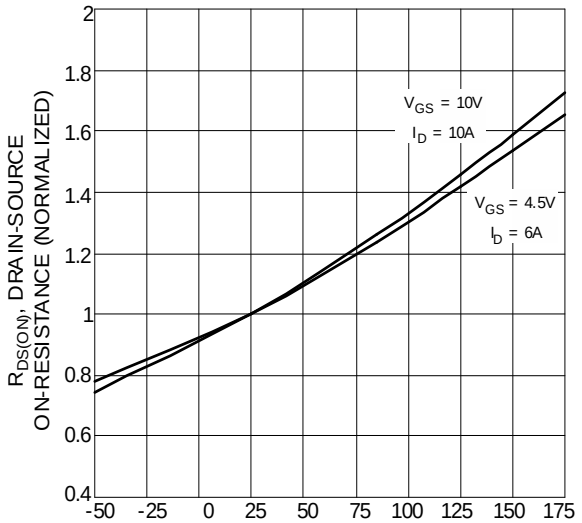


Figure 6 On-Resistance Variation with Temperature

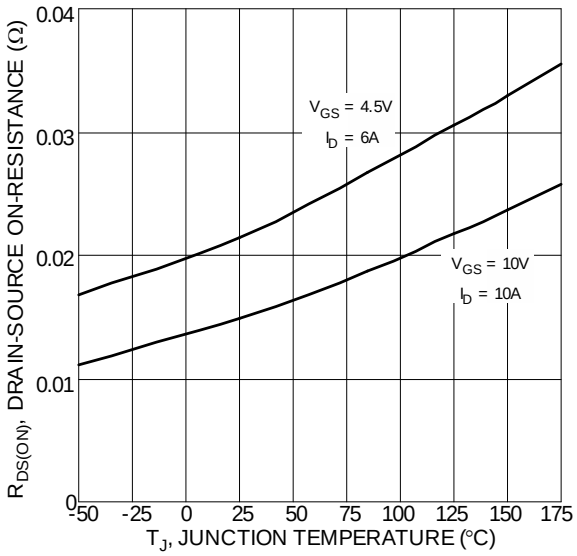


Figure 7 On-Resistance Variation with Temperature

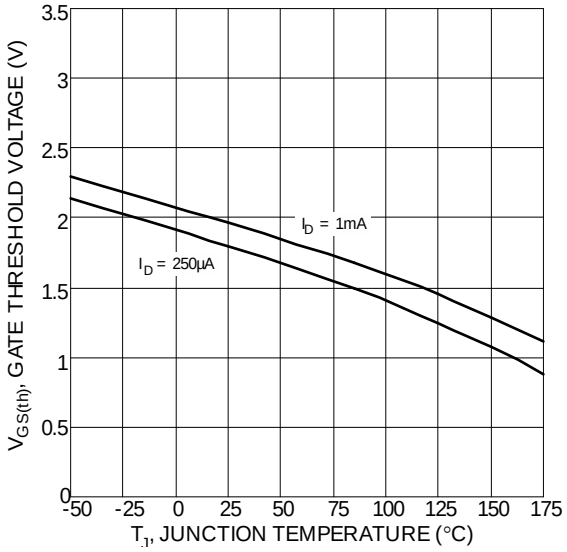


Figure 8 Gate Threshold Variation vs. Junction Temperature

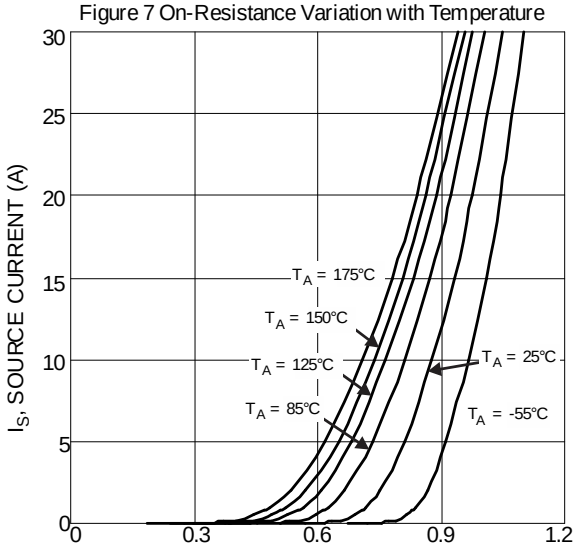


Figure 9 Diode Forward Voltage vs. Current

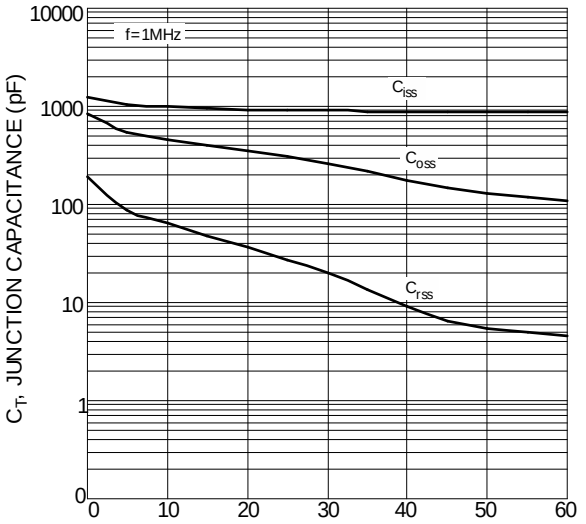


Figure 10 Typical Junction Capacitance

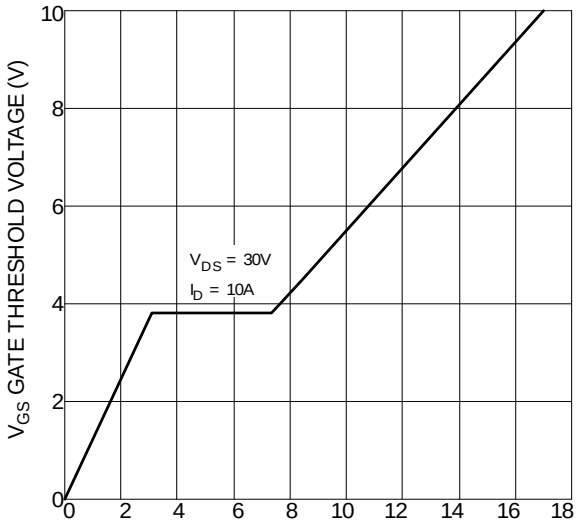


Figure 11 Gate Charge

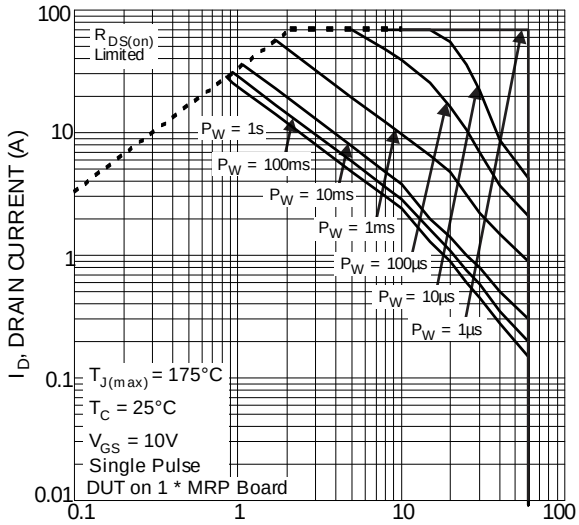


Figure 12 SOA, Safe Operation Area

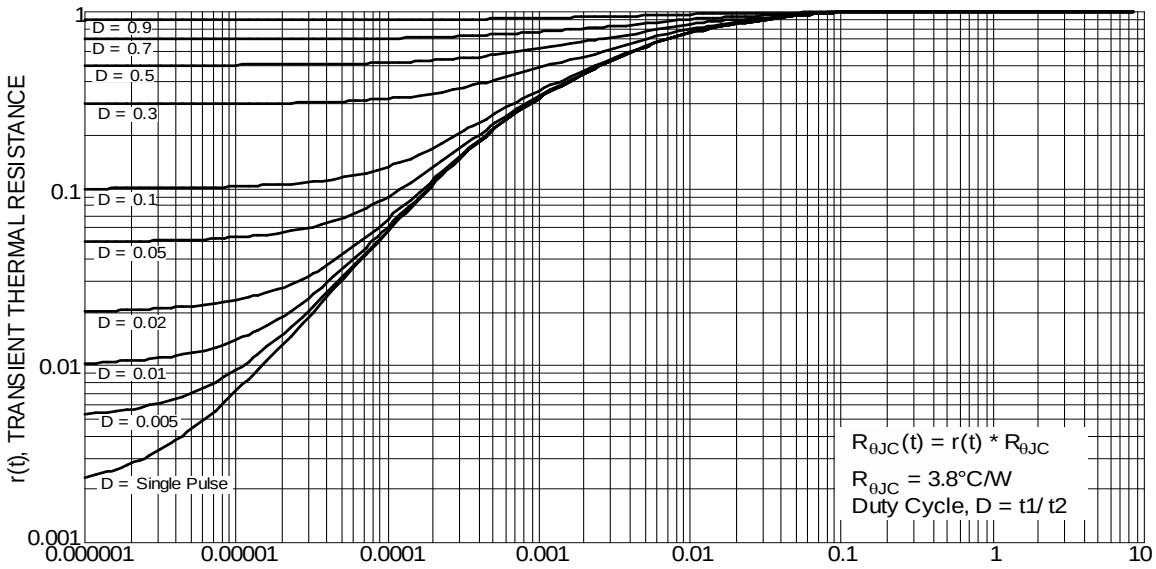
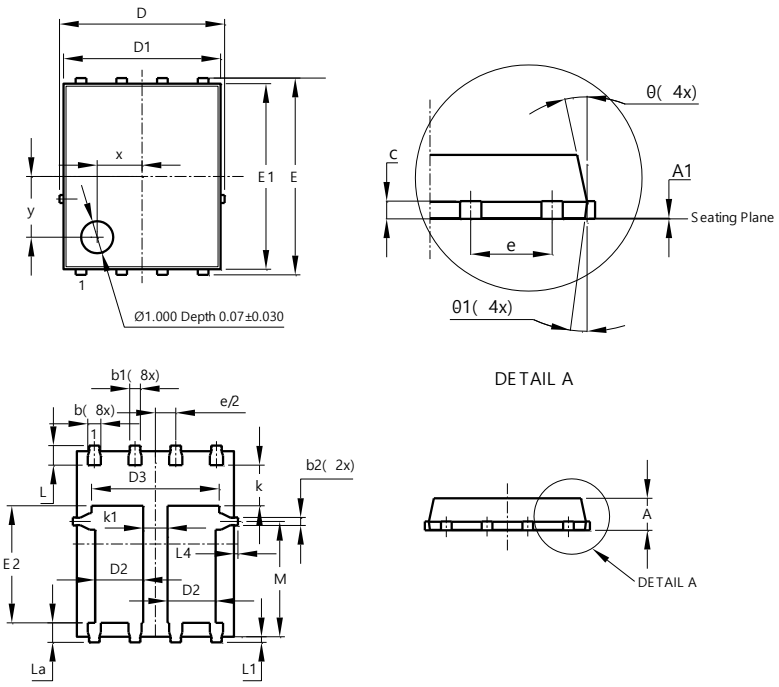


Figure 13 Transient Thermal Resistance

Package Outline Dimensions

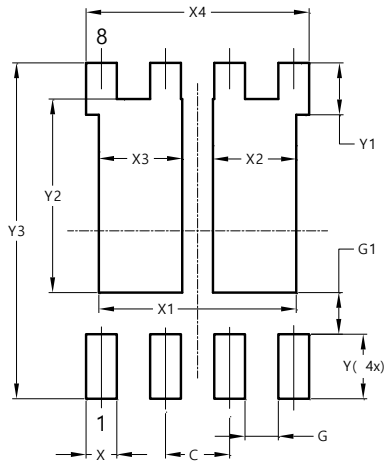
PowerDI5060-8 (Type C)



PowerDI5060-8 (Type C)			
Dim	**Min**	**Max**	**Typ**
A	0.90	1.10	1.00
A1	0	0.05	0.02
b	0.33	0.51	0.41
b1	0.300	0.366	0.333
b2	0.20	0.35	0.25
c	0.23	0.33	0.277
D	5.15 BSC		
D1	4.85	4.95	4.90
D2	1.40	1.60	1.50
D3	-	-	3.98
E	6.15 BSC		
E1	5.75	5.85	5.80
E2	3.56	3.76	3.66
e	1.27BSC		
k	-	-	1.27
k1	0.56	-	-
L	0.51	0.71	0.61
La	0.51	0.71	0.61
L1	0.05	0.20	0.175
L4	-	-	0.125
M	3.50	3.71	3.605
x	-	-	1.400
y	-	-	1.900
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

Suggested Pad Layout

PowerDI5060-8 (Type C)



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	3.910
X2	1.650
X3	1.650
X4	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610